

ULTRA LOW REVERSE LEAKAGE POWER SCHOTTKY RECTIFIER Very Low Voltage Drop

DESCRIPTION: 200 VOLT, 3.0 AMP, POWER SCHOTTKY RECTIFIER IN A HERMETIC SHD-1/B PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25\text{ }^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	200	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100\text{ }^\circ\text{C}$)	I_o	3.0	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t = 8.3\text{ms}$, Sine)	I_{FSM}	55	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_r=5\text{V}$) (per leg)	C_T	60	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R\theta_{JC}$	7.07	$^\circ\text{C/W}$
MAXIMUM OPERATING TEMPERATURE RANGE	T_{op}	-65 to +200	$^\circ\text{C}$
MAXIMUM STORAGE TEMPERATURE RANGE	T_{stg}	-65 to +175	$^\circ\text{C}$

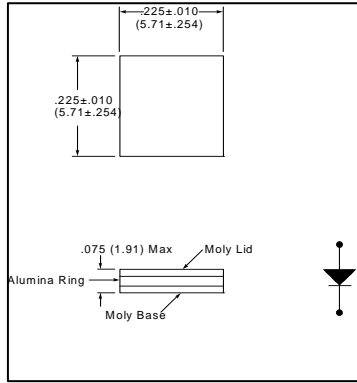
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 3.0\text{ Amps}$) $T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	V_f	0.92 0.76	Volts
MAXIMUM REVERSE CURRENT (I_r @ 200V PIV) $T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	I_r	0.025 0.2	mA
REVERSE RECOVERY TIME	t_{rr}	9	ns

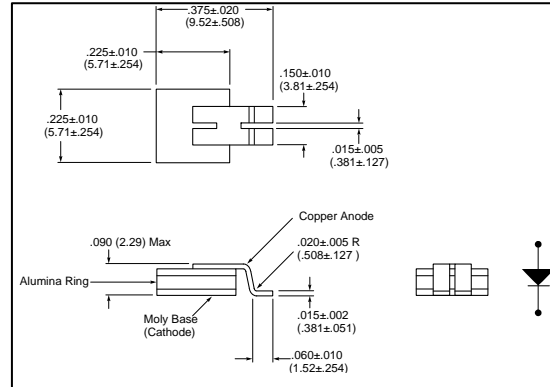
SENSITRON
TECHNICAL DATA
DATA SHEET 330, REV. C

MECHANICAL DIMENSIONS: In Inches / mm

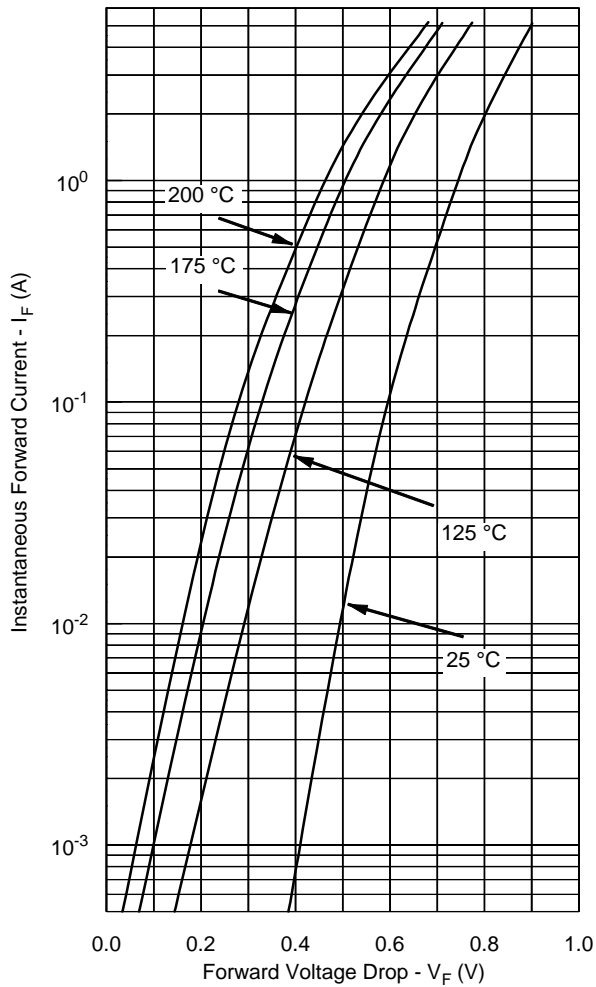
SHD-1



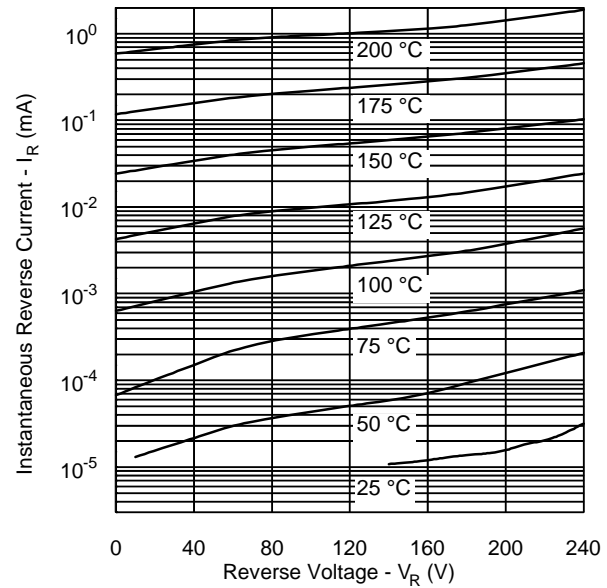
SHD-1B



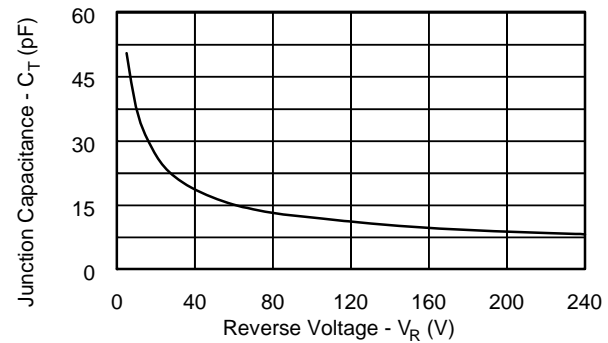
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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